



## Study of Bulk and Elementary Screw Dislocation Assisted Reverse Breakdown in Low-Voltage: Part 1: DC Properties

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BiblioGov. Paperback. Book Condition: New. This item is printed on demand. Paperback. 28 pages. Dimensions: 9.7in. x 7.4in. x 0.1in.Given the high density (approx. 10(exp 4)sq cm) of elementary screw dislocations (Burgers vector 1c with no hollow core) in commercial SiC wafers and epilayers, all appreciable current (greater than 1 A) SiC power devices will likely contain elementary screw dislocations for the foreseeable future. It is therefore important to ascertain the electrical impact of these defects, particularly in high-field vertical power device topologies where SiC is expected to enable large performance improvements in solid-state high-power systems. This paper compares the DC-measured reverse-breakdown characteristics of low-voltage (less than 250 V) small-area (less than 5 x 10(exp -4)sq cm) 4H-SiC p()n diodes with and without elementary screw dislocations. Compared to screw dislocation-free devices, diodes containing elementary screw dislocations exhibited higher pre-breakdown reverse leakage currents, softer reverse breakdown I-V knees, and highly localized microplasmic breakdown current filaments. The observed localized 4H-SiC breakdown parallels microplasmic breakdowns observed in silicon and other semiconductors, in which space-charge effects limit current conduction through the local microplasma as reverse bias is increased. This item ships from La Vergne, TN. Paperback.



## Reviews

The publication is great and fantastic. It can be filled with knowledge and wisdom You wont truly feel monotony at at any moment of your time (that's what catalogues are for about if you ask me).

-- Dr. Marcos Grimes III

Very useful to all of class of people. It is really simplified but unexpected situations within the 50 % in the ebook. I am delighted to let you know that this is actually the best book i have read in my personal daily life and can be he finest ebook for at any time.

-- Gwen Schultz